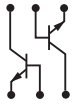
CMLT2222A
CMLT2222AG*

SURFACE MOUNT
DUAL NPN SMALL SIGNAL
SILICON SWITCHING TRANSISTORS

PICOmini™



SOT-563 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
These CENTRAL SEMICONDUCTOR devices consist of two (2) isolated 2222A NPN silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. These PICOmini™ devices have been designed for small signal general purpose and switching applications.

MARKING CODES: CMLT2222A: L22
CMLT2222AG*: 2CG

* Device is ***Halogen Free*** by design

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Power Dissipation (Note 1)	P_D	350	mW
Power Dissipation (Note 2)	P_D	300	mW
Power Dissipation (Note 3)	P_D	150	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_{CBO}	V_{CB}=60V		10	nA
I_{CBO}	V_{CB}=60V (T_A=125°C)		10	µA
I_{CEV}	V_{CE}=60V, V_{EB}=3.0V		10	nA
I_{EBO}	V_{EB}=3.0V		10	nA
BV_{CBO}	I_C=10µA	75		V
BV_{CEO}	I_C=10mA	40		V
BV_{EBO}	I_E=10µA	6.0		V
$V_{CE(SAT)}$	I_C=150mA, I_B=15mA		0.3	V
$V_{CE(SAT)}$	I_C=500mA, I_B=50mA		1.0	V
$V_{BE(SAT)}$	I_C=150mA, I_B=15mA	0.6	1.2	V
$V_{BE(SAT)}$	I_C=500mA, I_B=50mA		2.0	V
h_{FE}	V_{CE}=10V, I_C=0.1mA	35		
h_{FE}	V_{CE}=10V, I_C=1.0mA	50		
h_{FE}	V_{CE}=10V, I_C=10mA	75		
h_{FE}	V_{CE}=1.0V, I_C=150mA	50		
h_{FE}	V_{CE}=10V, I_C=150mA	100	300	
h_{FE}	V_{CE}=10V, I_C=500mA	40		

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0 mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0 mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4 mm²

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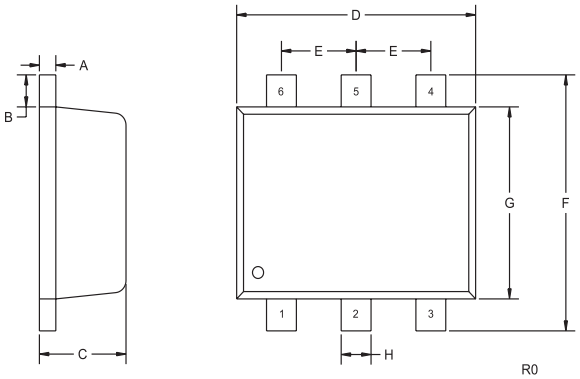
ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: (T_A=25°C unless otherwise noted)

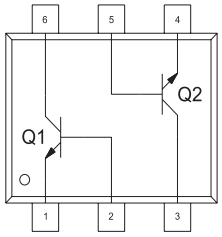
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	V_{CE}=20V, I_C=20mA, f=100MHz	300		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		8.0	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=1.0MHz		25	pF
h_{ie}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	2.0	8.0	kΩ
h_{ie}	V_{CE}=10V, I_C=10mA, f=1.0kHz	0.25	1.25	kΩ
h_{re}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz		8.0	$x10^{-4}$
h_{re}	V_{CE}=10V, I_C=10mA, f=1.0kHz		4.0	$x10^{-4}$
h_{fe}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	50	300	
h_{fe}	V_{CE}=10V, I_C=10mA, f=1.0kHz	75	375	
h_{oe}	V_{CE}=10V, I_C=1.0mA, f=1.0kHz	5.0	35	µS
h_{oe}	V_{CE}=10V, I_C=10mA, f=1.0kHz	25	200	µS
$rb'C_c$	V_{CB}=10V, I_E=20mA, f=31.8MHz		150	ps
NF	V_{CE}=10V, I_C=100mA, R_S=1.0kΩ, f=1.0kHz		4.0	dB
t_d	V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA		10	ns
t_r	V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA		25	ns
t_s	V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA		225	ns
t_f	V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA		60	ns

SOT-563 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)



LEAD CODE:
1) EMITTER Q1
2) BASE Q1
3) COLLECTOR Q2
4) EMITTER Q2
5) BASE Q2
6) COLLECTOR Q1

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R2 (6-March 2009)